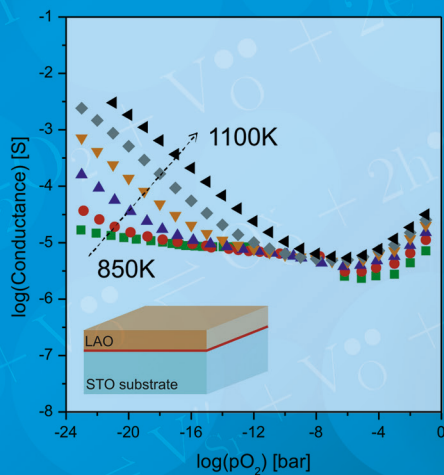
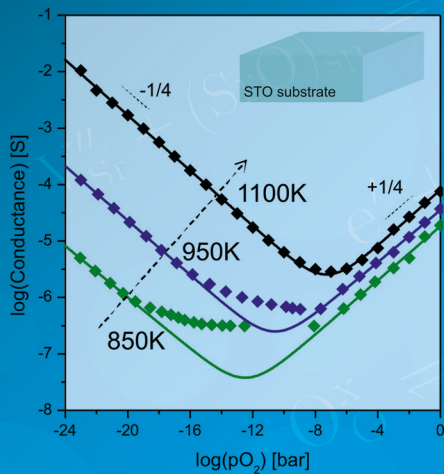




The role of defects at functional interfaces between polar and non-polar perovskite oxides

Felix Gunkel

Forschungszentrum Jülich GmbH
Peter Grünberg Institute (PGI)
Electronic Materials (PGI-7)

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